

深圳市晶泰源电子有限公司

JTY D882

TRANSISTOR(NPN)

FEATURES

Power dissipation

PCM:1W(Tamb=25°C)

Collector current

ICM:2.0A

Collector-base voltage

V(BR)CBO: 40V

Operating and storage junction temperature range

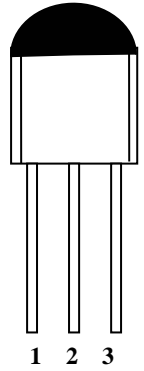
TJ,Tstg:-65°C to -150°C

T0-92

1. EMITTER

2. COLLECTOR

3. BASE



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	Ic=1mA, IE=0	40			V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=1mA, IB=0	30			V
Emitter-base breakdown voltage	V(BR)EBO	Ic=-1mA, Ic=0	6			V
Collector cut-off current	ICBO	Vcb=40V, IE=0			0.5	μA
Collector cut-off current	IcEo	Vce=30V, IB=0			1.0	μA
Emitter cut-off current	IEBO	VEB=6V, Ic=0			0.1	μA
DC current gain	HFE	Vce=5V, Ic=1mA	200		400	
Collector-emitter saturation voltage	VCE(sat)	Ic=2A, IB=200mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	Ic=2A, IB=200mA			2.0	V
Transition frequency	fT	Vce=10V, Ic=50mA f=30MHZ	50			MHZ

CLASSIFICATION OF hFE(2)

Rank	P	
Range	300-400	